

查询ARF2012供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

ANSALDO

Ansaldo Trasporti s.p.a.
Unita' Semiconduttori

Via N. Lorenzi 8 - I 16152 GENOVA - ITALY
Tel. int. +39/(0)10 6556549 - (0)10 6556488
Fax Int. +39/(0)10 6442510
Tx 270318 ANSUSE I -

FAST RECOVERY DIODE

ARF2012

Repetitive voltage up to **2600 V**
Mean forward current **1525 A**
Surge current **16 kA**

FINAL SPECIFICATION

apr 97 - ISSUE : 04

Symbol	Characteristic	Conditions	T _j [°C]	Value	Unit
BLOCKING					
V _{RRM}	Repetitive peak reverse voltage		150	2600	V
V _{RSM}	Non-repetitive peak reverse voltage		150	2700	V
I _{RRM}	Repetitive peak reverse current	V=VRRM	150	50	mA
CONDUCTING					
I _{F(AV)}	Mean forward current	180° sin ,50 Hz, Th=55°C, double side cooled		1525	A
I _{F(AV)}	Mean forward current	180° square,50 Hz,Th=55°C,double side cooled		1545	A
I _{FSM}	Surge forward current	Sine wave, 10 ms	150	16	kA
I ² t	I ² t	reapplied reverse voltage up to 50% VRSM		1280 x1E3	A²s
V _{FM}	Forward voltage	Forward current 3400 A	25	2.5	V
V _{F(TO)}	Threshold voltage		150	1.03	V
r _F	Forward slope resistance		150	0.362	mohm
SWITCHING					
t _{rr}	Reverse recovery time	I _F = 1000 A di/dt= 100 A/μs VR = 100 V	150	4.6	μs
Q _{rr}	Reverse recovery charge			800	μC
I _{rr}	Peak reverse recovery current			345	A
s	Softness (s-factor), min			0.4	
V _{FR}	Peak forward recovery	di/dt= 400 A/μs	150	13	V
MOUNTING					
R _{th(j-h)}	Thermal impedance	Junction to heatsink, double side cooled		26	°C/kW
T _j	Operating junction temperature			-30 / 150	°C
F	Mounting force			18.0 / 20.0	kN
	Mass			500	g

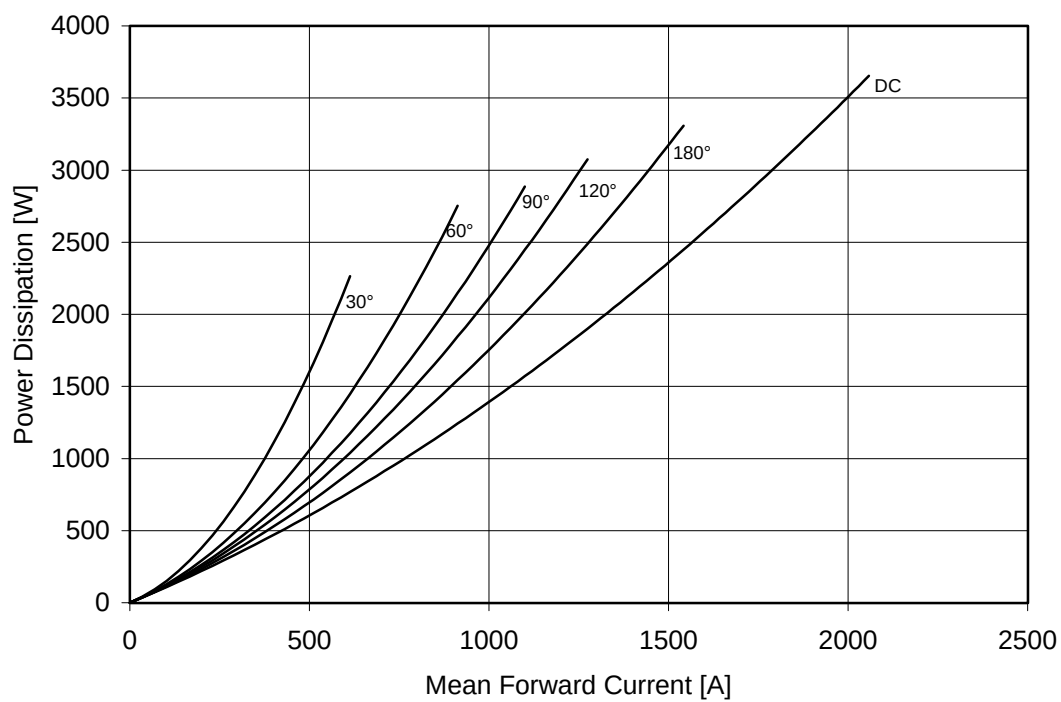
ORDERING INFORMATION : ARF2012 S 26

standard specification ☐ VRRM/100 ☐

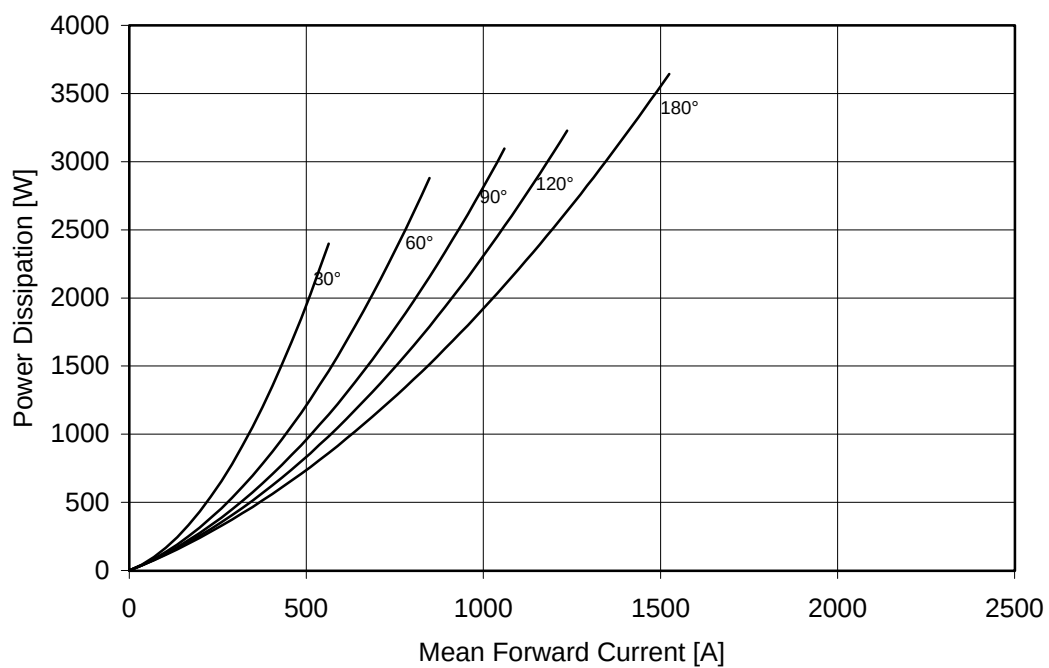


DISSIPATION CHARACTERISTICS

SQUARE WAVE

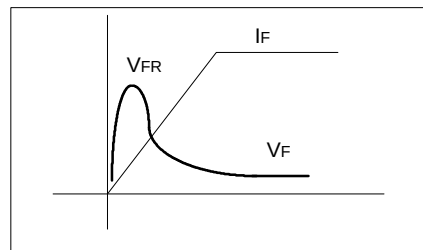
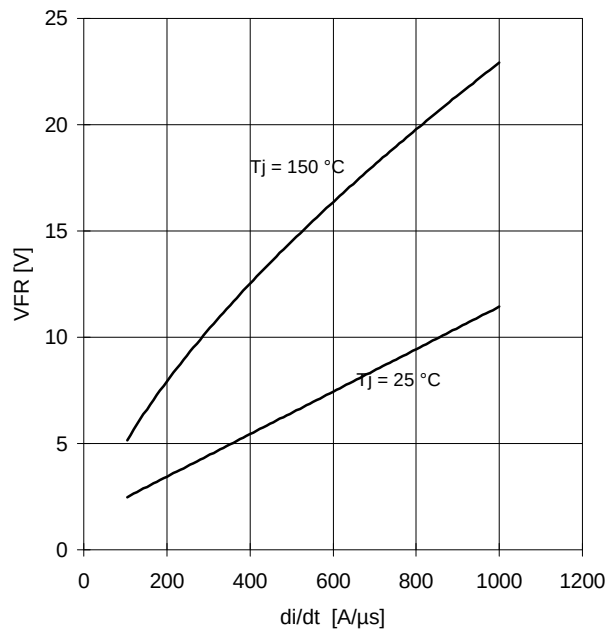


SINE WAVE

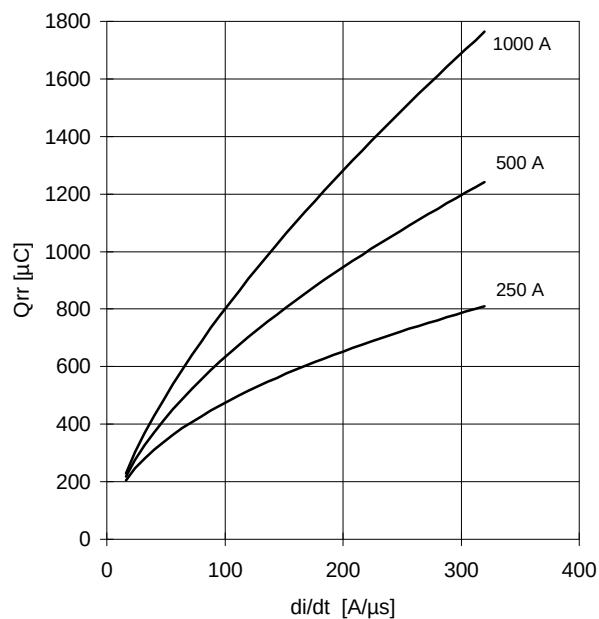


SWITCHING CHARACTERISTICS

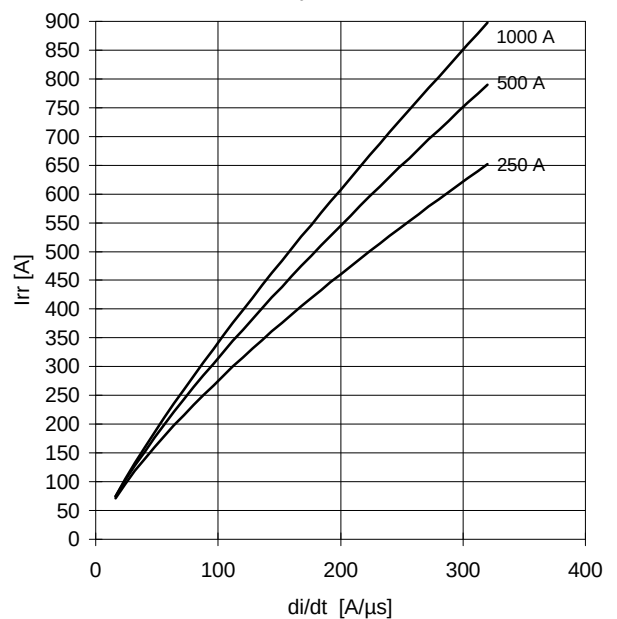
FORWARD RECOVERY VOLTAGE



REVERSE RECOVERY CHARGE
Tj = 150 °C



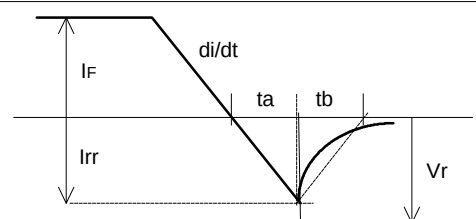
REVERSE RECOVERY CURRENT
Tj = 150 °C



$$t_a = I_{rr} / (di/dt) \quad t_b = t_{rr} - t_a$$

$$\text{Softness (s factor)} \quad s = t_b / t_a$$

$$\text{Energy dissipation during recovery } E_r = V_r \cdot (Q_{rr} - I_{rr} \cdot t_a / 2)$$

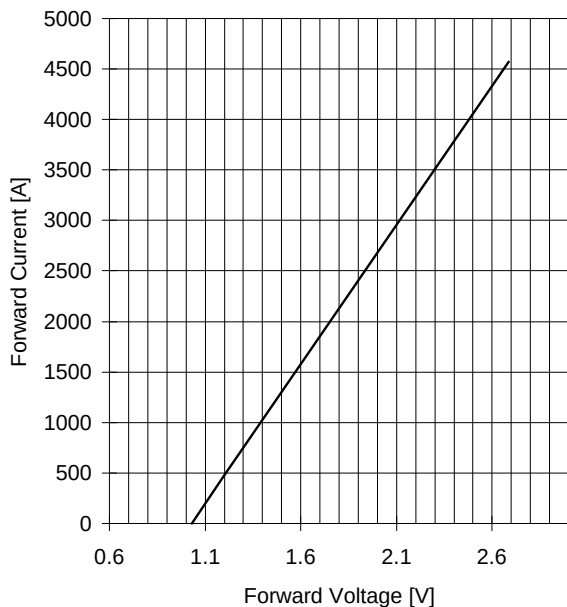


ARF2012 FAST RECOVERY DIODE

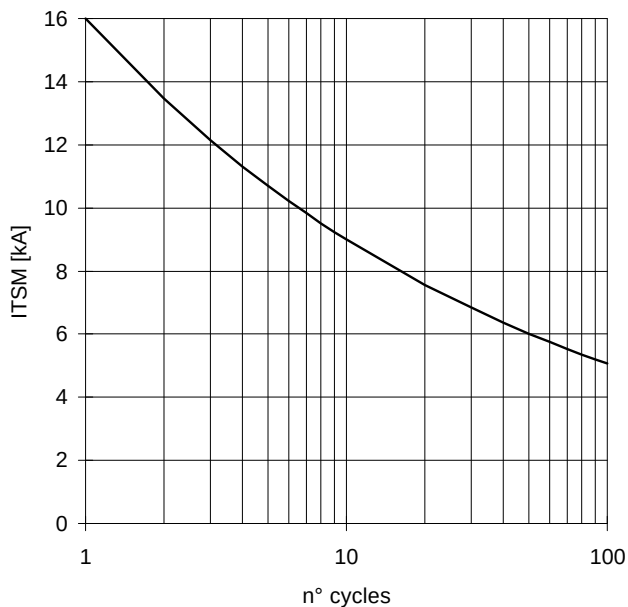
ANSALDO

FINAL SPECIFICATION apr 97 - ISSUE : 04

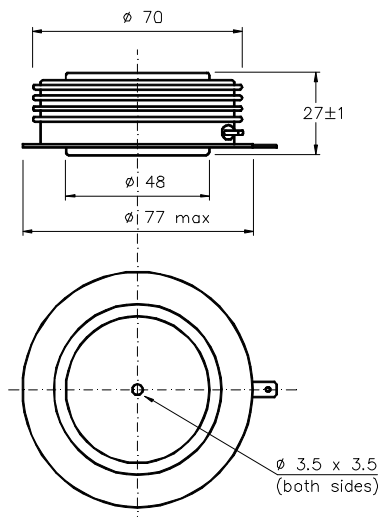
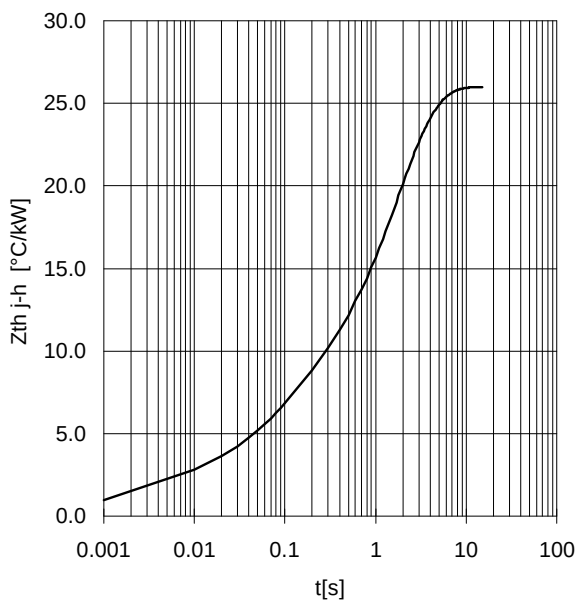
FORWARD CHARACTERISTIC
 $T_j = 150^\circ\text{C}$



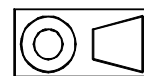
SURGE CHARACTERISTIC
 $T_j = 150^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED



Dimensions
in mm



All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness $< .03$ mm and roughness $< 2 \mu\text{m}$.

In the interest of product improvement ANSALDO reserves the right to change any data given in this data sheet at any time without previous notice.

If not stated otherwise the maximum value of ratings (symbols over shaded background) and characteristics is reported.

Distributed by

